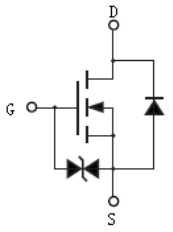
Super Junction Power MOSFET
SJM80R850D

Features

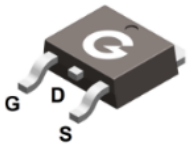
- Low power loss by high speed switching and low on-resistance
- Excellent thermal behavior
- Very low FOM for fast switching efficiency
- Integrated ESD protection diode：HBM: JESD22-A114-B: 3A
- RoHS compliant with Halogen-free

HF



Applications

- PFC power supply stages
- Lighting applications
- Adapter



Mechanical Data

- Case: TO-252
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208

TO-252

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
SJM80R850D	TO-252	80 pcs / Tube & 2500 pcs / Tape & Reel	SJM80R850D

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V_{DSS}	800	V
Gate-to-Source Voltage (Static)	V_{GSS}	±20	V
Continuous Drain Current (T_C = 25°C)	I_D	6.5	A
Continuous Drain Current (T_C = 100°C)		4.1	A
Pulsed Drain Current (t_p = 10μs, T_C = 25°C)	I_{DM}	26	A
Single Pulse Avalanche Energy *3	E_{AS}	120	mJ
Power Dissipation (T_C = 25°C)	P_D	63	W
Operating Junction Temperature Range	T_J	-55 ~ +150	°C
Storage Temperature Range	T_{STG}	-55 ~ +150	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	$R_{\theta JC}$	-	1.4	2	°C/W
Thermal Resistance Junction-to-Air *1	$R_{\theta JA}$	-	50	62	°C/W

Electrical Characteristics (@ T_A = 25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V_{DSS}	Drain-Source Breakdown Voltage	V_{GS} = 0V, I_D = 250μA	800	-	-	V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS} = 800V, V_{GS} = 0V	-	-	1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS} = ±20V, V_{DS} = 0V	-	-	±1	μA
On Characteristics						
$R_{DS(ON)}$	Drain-Source On-resistance *2	V_{GS} = 10V, I_D = 1.5A	-	0.68	0.85	Ω
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS} = V_{GS}, I_D = 250μA	2	3.2	4	V
R_G	Gate Resistance	V_{GS} = 0V, f = 1MHz	-	7	-	Ω
Dynamic Characteristics						
C_{ISS}	Input Capacitance	V_{GS} = 0V V_{DS} = 40V f = 250kHz	-	601	-	pF
C_{OSS}	Output Capacitance		-	54	-	
C_{RSS}	Reverse Transfer Capacitance		-	2.4	-	
Switching Characteristics						
$t_{d(ON)}$	Turn-on Delay Time *4	V_{DD} = 400V I_D = 2.8A R_G = 25Ω	-	23	-	ns
t_r	Turn-on Rise Time *4		-	18	-	
$t_{d(OFF)}$	Turn-Off Delay Time *4		-	74	-	
t_f	Turn-Off Fall Time *4		-	17	-	
Q_G	Total Gate-Charge	V_{DD} = 640V V_{GS} = 10V I_D = 3A	-	17	-	nC
Q_{GS}	Gate to Source Charge		-	3	-	
Q_{GD}	Gate to Drain (Miller) Charge		-	8.4	-	
Source-Drain Diode Characteristics						
V_{SD}	Diode Forward Voltage *2	I_{SD} = 3A, V_{GS} = 0V	-	0.85	1.3	V
t_{rr}	Reverse Recovery Time	I_F = 1A, V_R = 400V dI/dt = 100A/μs	-	190	-	ns
Q_{rr}	Reverse Recovery Charge		-	1	-	μC

Notes:

1. The data tested by surface mounted on a minimum recommended FR-4 board
2. The data tested by pulsed, pulse width ≤ 300μs, duty cycle ≤ 2%
3. The E_{AS} data shows Max. rating. The test condition is V_{DD} = 100V, V_{GS} = 10V, L = 50mH
4. Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ T_A = 25°C unless otherwise specified)

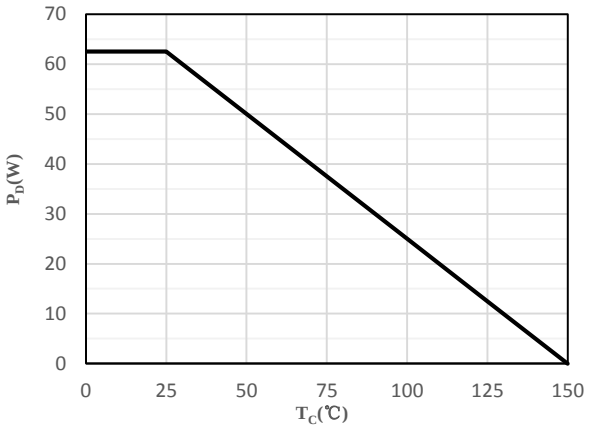


Fig 1 Power Dissipation

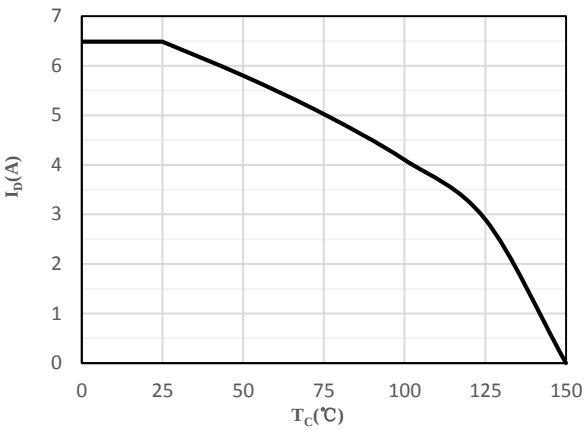


Fig 2 Drain Current

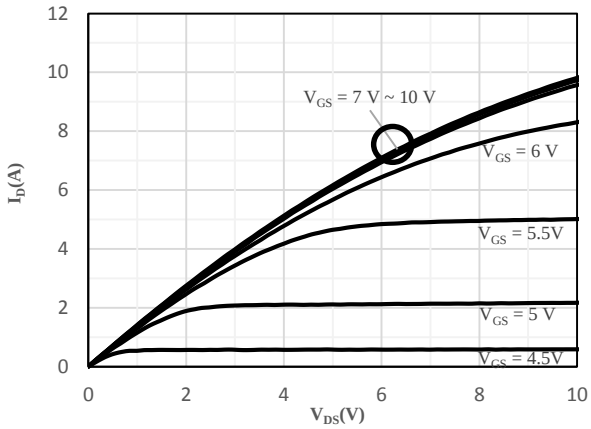


Fig 3 Typical Output Characteristics

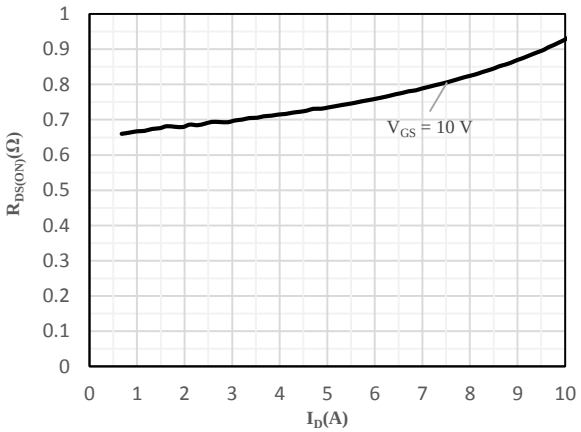


Fig 4 On-Resistance vs. Drain Current and Gate Voltage

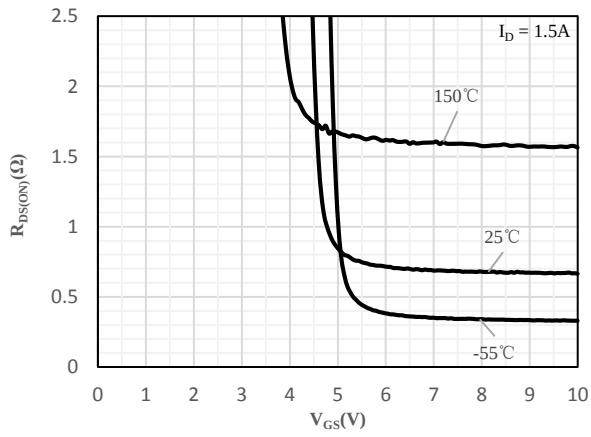


Fig 5 On-Resistance vs. Gate-Source Voltage

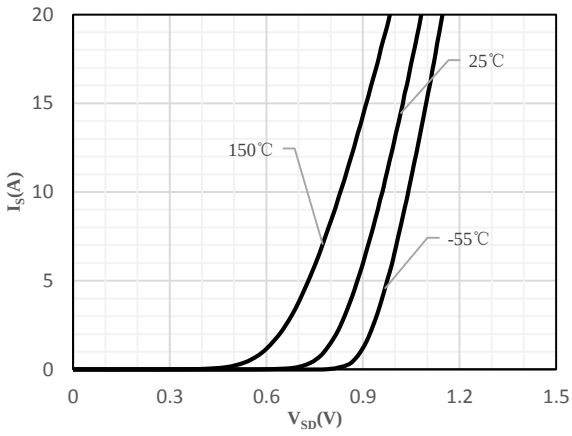


Fig 6 Body-Diode Characteristics

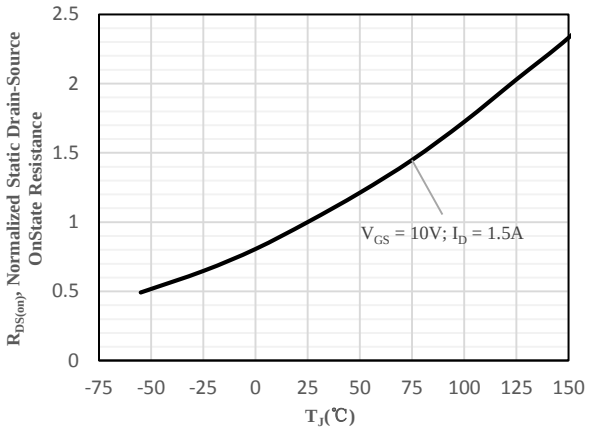


Fig 7 Normalized On-Resistance vs. Junction Temperature

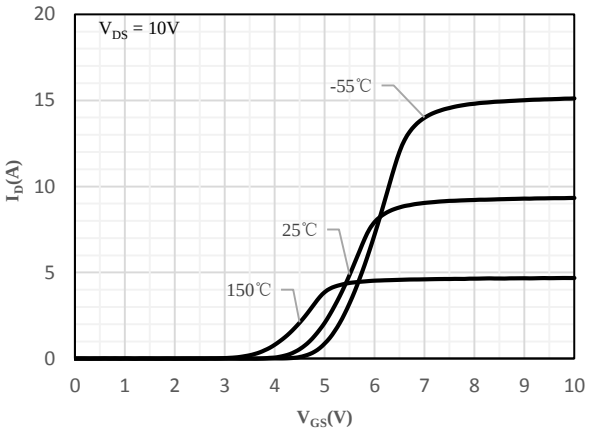


Fig 8 Transfer Characteristics

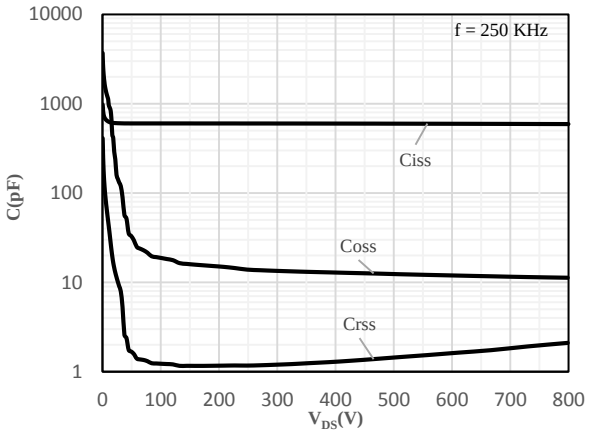


Fig 9 Capacitance Characteristics

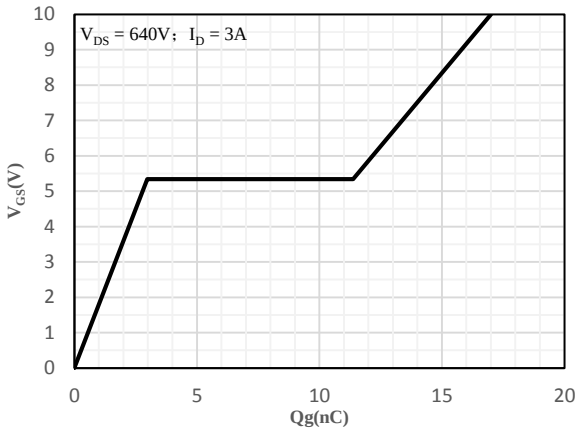


Fig 10 Gate-Charge Characteristics

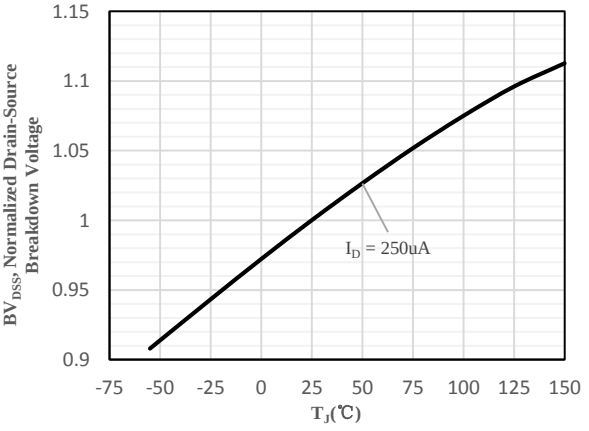


Fig 11 Normalized Breakdown Voltage vs. Junction Temperature

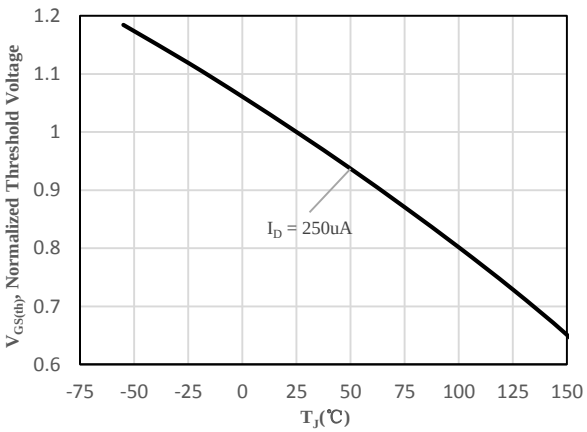


Fig 12 Normalized $V_{GS(th)}$ vs. Junction Temperature

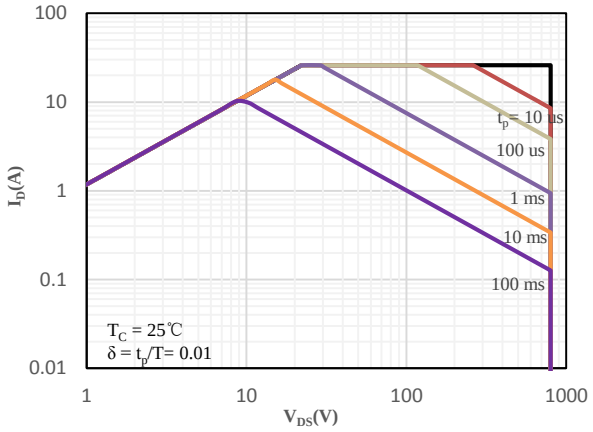


Fig 13 Safe Operation Area

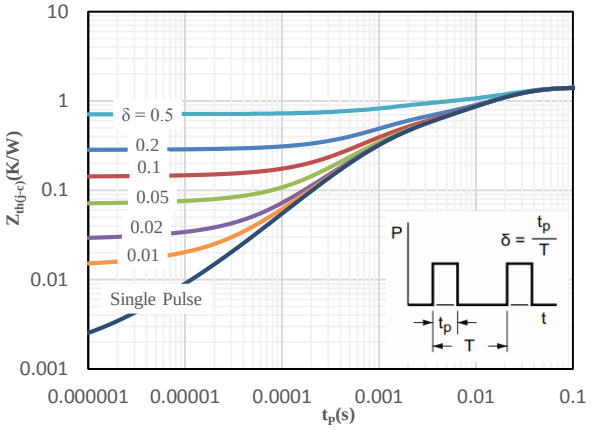
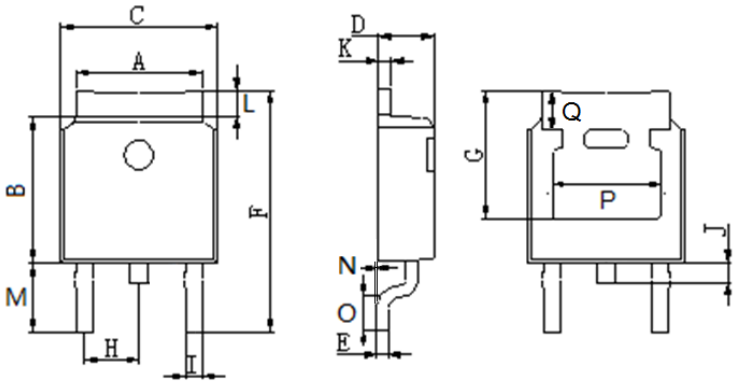


Fig 14 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



TO-252		
Dimension	**Min.**	**Max.**
A	5.05	5.65
B	5.80	6.40
C	6.25	6.85
D	2.20	2.40
E	0.40	0.60
F	9.71	10.31
G	5.05	5.65
H	2.10	2.50
I	0.70	0.90
J	0.50	0.70
K	0.40	0.60
L	0.80	1.20
M	2.70	3.10
N	0.00	0.12
O	1.30	1.70
P	4.70	4.90
Q	1.25	1.45

Mounting Pad Layout (Unit: mm)

TO-252